3

The ZM150N03T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

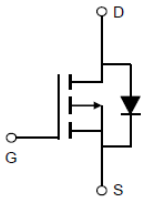
2

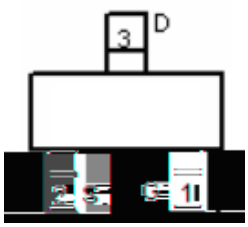
Advance high cell density Trench technology

$_{DS(ON)}$ to minimize conductive loss

nd Synchronous Rectifier

Product Summary





Part NO.	ZM150N03T
Marking	150N03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

T_C =25

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	$I_{D@}$TC=25	8	A
	$I_{D@}$TC=75	6.1	A
	$I_{D@}$TC=100	5	A
Pulsed Drain Current	I_{DM}	16	A
Total Power Dissipation	P_D	10	W
Total Power Dissipation(TA=25)	P_D@TA=25	0.7	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	40	mJ

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}			94.8912	

Fig.1 Power Dissipation Derating Curve

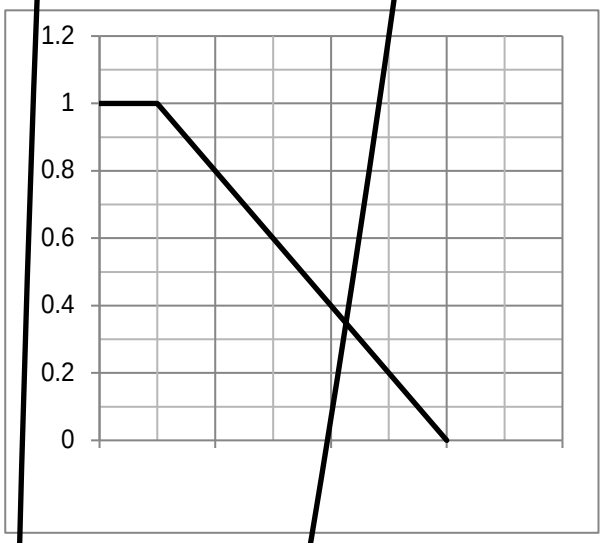


Fig.2 Typical output Characteristics

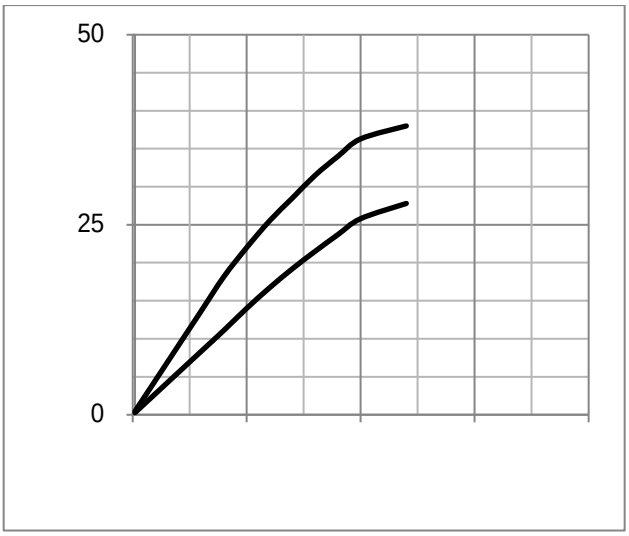


Fig.3 Threshold Voltage V.S Junction Temperature

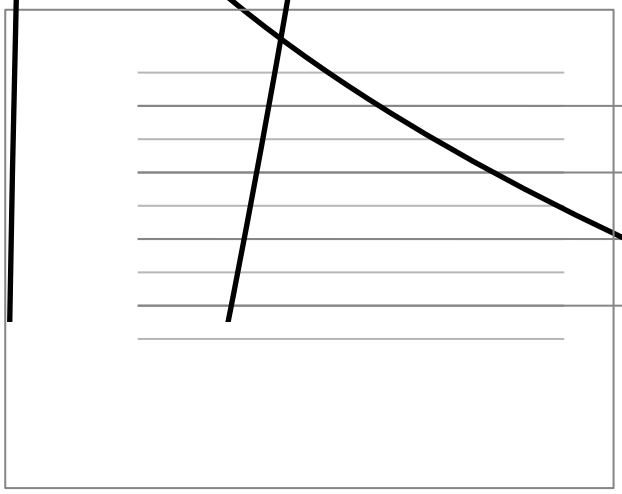
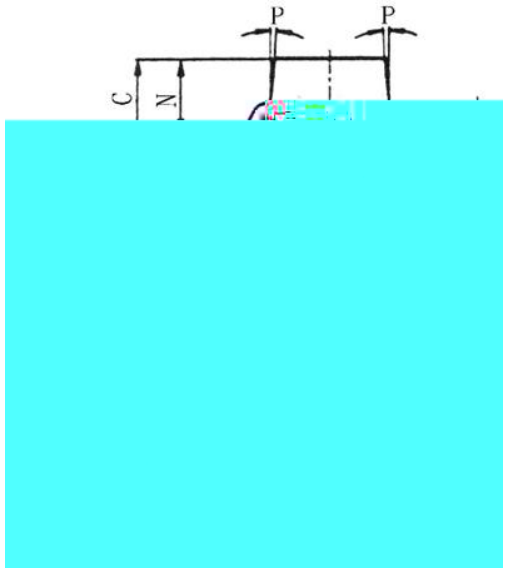


Fig.4 Resistance V.S Drain Current

(SOT23)

Unit mm



SYMBOL	min	nom	max
A	2.70	2.9	3.10
B	1.15	1.3	1.50
C			1.30
D	0.35	0.4	0.55
E	2.20	2.4	2.70
G	1.70	1.9	2.10
H	0.85	0.95	1.05
J	0.05	0.10	0.20
K	0.00		0.10
L	0.45	0.55	0.65

M	0.20		
N	0.90	1.00	1.20
P		7°	